



Monolayer Graphene

Transparency: >97%

Graphene Coverage: 100% with sporadic adlayers (see optical image above)

FET mobility*: >2700 cm²/(V·s)

Sheet resistance*: 430 ± 50 Ω/sq

Grain size: >40 μm

Raman D/G ratio: Indistinguishable to 0.03

Substrate

Our 6-inch Si/SiO₂ wafers are sourced from a reliable, quality-assured supplier.

Type/Doping: P/B

Wafer Thickness : 675 +/- 25 μm

Oxide Thickness: 300 nm

Resistivity: 1 – 10 (ohm-cm)

Orientation: <1-0-0>

Growth Method: CZ

Metal Impurities: 1.00e10 – 5.00e10 (at/cm²)Substrate